

IN THE SPECIFICATION

Please replace the paragraph starting on page 2, line 5 with the following rewritten paragraph.

§ 1
A gate oxide film and a gate electrode are sequentially formed on some region of a semiconductor substrate 10, and source and drain regions are formed in the semiconductor substrate 10 at both sides of the gate electrode (not shown).

Please replace the paragraph starting on page 6, line 1 with the following rewritten paragraph.

§ 2
The method for fabricating a capacitor of a semiconductor device according to the present invention is performed in such a manner that a conductive layer is deposited on a semiconductor substrate 110. A photoresist pattern is then formed on the conductive layer, and the conductive layer is etched using the photoresist as a mask to form a lower electrode. The photoresist is then removed using an etching gas having no volatility with respect to the lower electrode, and a dielectric film and an upper electrode are thereafter sequentially formed on a surface of the lower electrode.

Please replace the paragraph starting on page 6, line 17 with the following rewritten paragraph.

B3
A gate oxide film and a gate electrode are sequentially formed on a region of a semiconductor substrate 110, and source and drain regions are formed in the semiconductor substrate 110 at both sides of the gate electrode (not shown).

Please replace the paragraph starting on page 6, line 22 and ending on page 7, with the following rewritten paragraph.

B4
A conductive material such as polysilicon or tungsten, or another conductive material having low resistance is then deposited on the interleaving insulating film 101 including in the contact hole. A contact plug 102 is formed within the contact hole by an etch-back process or a chemical mechanical polishing process so that the conductive material is only formed within the contact hole.

IN THE CLAIMS

Please amend the claims as follows.

- B5
7. (Amended) The method of claim 4, wherein the insulating film patterns comprise an oxide film.
 8. (Amended) The method of claim 4, wherein the insulating film patterns are formed by stacking two insulating films.